

12 V, 5.3 A NPN low VCEsat transistor

6 February 2024

**Product data sheet** 

### 1. General description

NPN low V<sub>CEsat</sub> transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS301PX-Q

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- + High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

### 3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control

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- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick I	reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	12	V
I <sub>C</sub>	collector current		-	-	5.3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	10.6	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	28	40	mΩ

# nexperia

### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base		B
			3 2 1	E
			SOT89	sym123

### 6. Ordering information

Table 3. Ordering information						
Type number Package						
	Name	Description	Version			
PBSS301NX-Q		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<u>SOT89</u>			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code[1]
PBSS301NX-Q	%5B

[1] % = placeholder for manufacturing site code

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

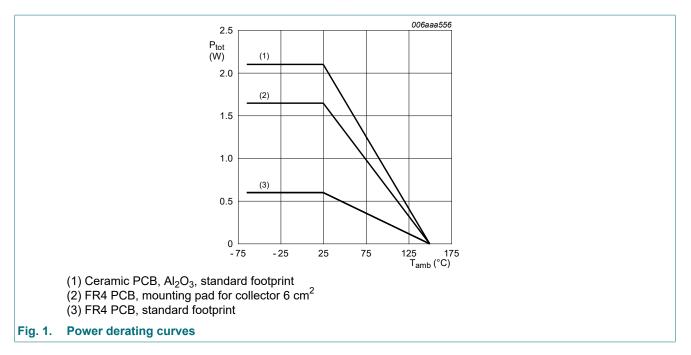
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	12	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	12	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
l <sub>C</sub>	collector current			-	5.3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	10.6	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

#### 12 V, 5.3 A NPN low VCEsat transistor



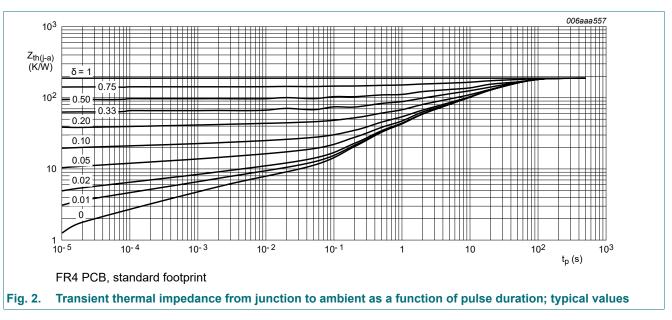
### 9. Thermal characteristics

#### Table 6. Thermal characteristics Parameter Conditions Min Unit Symbol Max Тур 208 K/W thermal resistance from in free air [1] R<sub>th(j-a)</sub> junction to ambient K/W [2] 76 K/W [3] 60 $R_{th(j-sp)}$ thermal resistance from 20 K/W junction to solder point

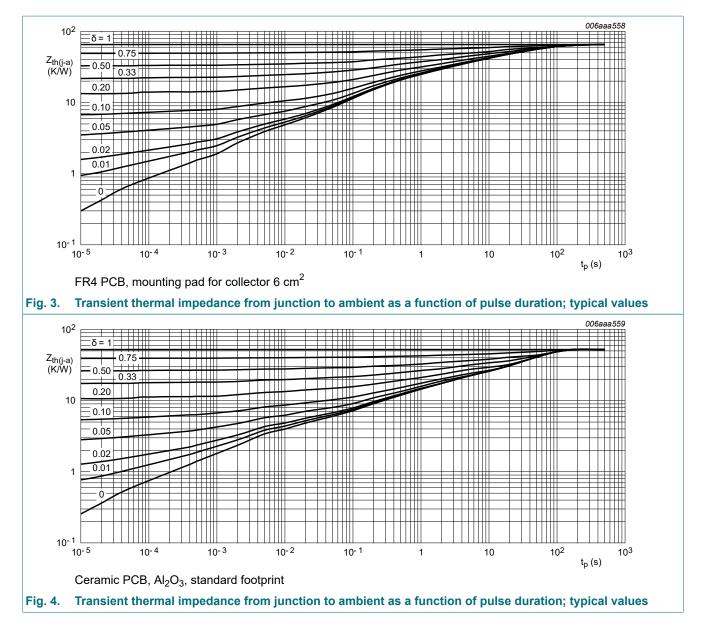
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



#### 12 V, 5.3 A NPN low VCEsat transistor



PBSS301NX-Q

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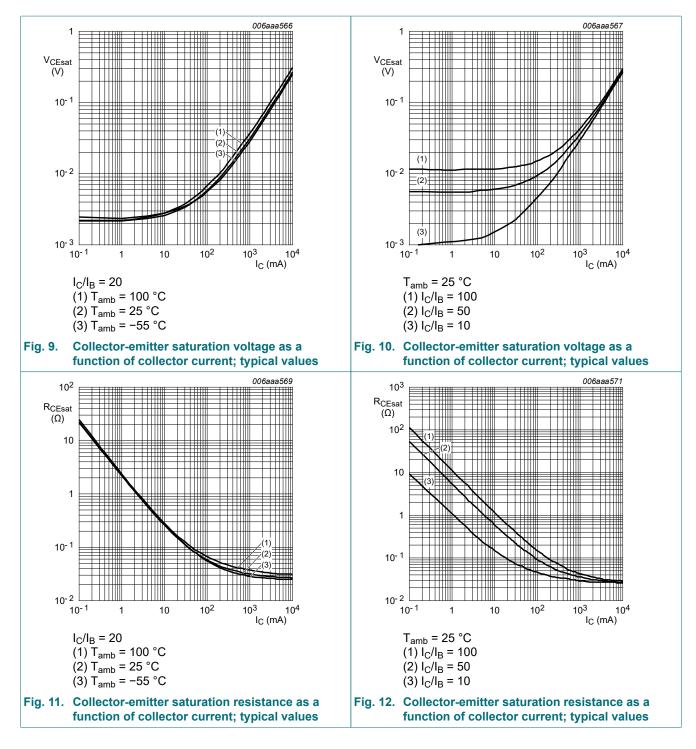
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
сво	collector-base cut-off	V <sub>CB</sub> = 12 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 12 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
EBO	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
η <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; I <sub>C</sub> = 0.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	300	530	-	
		$    V_{CE} = 2 \text{ V; } I_C = 1 \text{ A; pulsed; } t_p \le 300  \mu\text{s;} \\    \delta \le 0.02;  T_{amb} = 25 ^\circ\text{C} $	300	520	-	
			250	480	-	
			200	420	-	
		$    V_{CE} = 2 \text{ V};  I_{C} = 6 \text{ A}; \text{ pulsed};  t_{p} \leq 300  \mu\text{s}; \\    \delta \leq 0.02;  T_{amb} = 25 ^{\circ}\text{C} $	200	340	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = 0.5$ A; $I_{B} = 50$ mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; $T_{amb} = 25$ °C	-	18	25	mV
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	35	50	mV
		$I_{C}$ = 1 A; $I_{B}$ = 10 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	50	70	mV
		$I_{C}$ = 2 A; $I_{B}$ = 40 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	70	100	mV
		$I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	110	160	mV
		$I_{C}$ = 4 A; $I_{B}$ = 400 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	100	140	mV
		$I_{C}$ = 4 A; $I_{B}$ = 40 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	125	190	mV
		$I_C$ = 5.3 A; $I_B$ = 265 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	140	200	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = 4$ A; $I_B = 200$ mA; pulsed; $t_p \le 300$ μs; δ $\le 0.02$ ; $T_{amb} = 25$ °C	-	28	40	mΩ
		I <sub>C</sub> = 4 A; I <sub>B</sub> = 40 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	32	48	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	0.81	0.9	V
		$I_C = 4 \text{ A}; I_B = 400 \text{ mA}; \text{ pulsed}; t_p \le 300 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	0.92	1.05	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$ \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 2 A; pulsed; } t_{p} \texttt{\leq } 300 \ \texttt{\mu}s; \\ \delta \texttt{\leq } 0.02; \ T_{amb} \texttt{= 25 °C} \end{array} $	-	0.75	0.85	V
d	delay time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 3 A; I <sub>Bon</sub> = 0.15 A;	-	15	-	ns
r	rise time	I <sub>Boff</sub> = -0.15 A; T <sub>amb</sub> = 25 °C	-	40	-	ns
on	turn-on time		-	55	-	ns
s	storage time	] [	-	195	-	ns
f	fall time		-	75	-	ns
off	turn-off time		-	270	-	ns

### 12 V, 5.3 A NPN low VCEsat transistor

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 3 A T <sub>amb</sub> = 25 °C	; f = 100 MHz;	-	140	-	MHz
Cc	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A T <sub>amb</sub> = 25 °C	; i <sub>e</sub> = 0 A; f = 1 MHz;	-	125	160	pF
		Ginz					
1000		006aaa564	. 14			006aaa570	
h <sub>FE</sub>			I <sub>C</sub> (A)		IB (n	nA) = 50	
			12			45-	
800			10			40-	
(2)							
600			8			25 -	
			E-			20 - 15	
400			6			10	
(3)			4				
200						5	
			2				
0			o 📕 🗌				
10 <sup>-1</sup>	1 10 10 <sup>2</sup>	10 <sup>3</sup> 10 <sup>4</sup> I <sub>C</sub> (mA)	0 1	2 3	4	5 V <sub>CE</sub> (V)	
V <sub>CE</sub> =	2 \/		T <sub>amb</sub> = 25 °C			VCE (V)	
(1) T <sub>a</sub>	<sub>mb</sub> = 100 °C		Fig. 6. Collector cur	ront as a fu	nction o	of collect	tor-
(2) T <sub>a</sub>	<sub>mb</sub> = 25 °C		emitter voltag				
	<sub>mb</sub> = −55 °C						
	urrent gain as a function nt; typical values	of collector					
1.2		006aaa565	1.2			006aaa568	
VBE			V <sub>BEsat</sub>				
(V)			(V)				
0.8			0.8				
(1)							
			(2)				
(2)							
0.4			0.4 (3)				
(3)							
0			0				
10 <sup>-1</sup>	1 10 10 <sup>2</sup>	10 <sup>3</sup> 10 <sup>4</sup> I <sub>C</sub> (mA)	10 <sup>-1</sup> 1	10 10		<sup>3</sup> 10 <sup>4</sup> I <sub>C</sub> (mA)	
V <sub>CE</sub> =	2 V	,	I <sub>C</sub> /I <sub>B</sub> = 20				
(1) T <sub>a</sub>	<sub>mb</sub> = −55 °C		(1) T <sub>amb</sub> = −55				
(2) T <sub>a</sub> (3) T	<sub>mb</sub> = 25 °C <sub>mb</sub> = 100 °C		(2) T <sub>amb</sub> = 25 (3) T <sub>amb</sub> = 100				
	-emitter voltage as a fun	ction of collector	Fig. 8. Base-emitter		voltage	as a fun	ction c
	nt; typical values		collector cur				

#### 12 V, 5.3 A NPN low VCEsat transistor



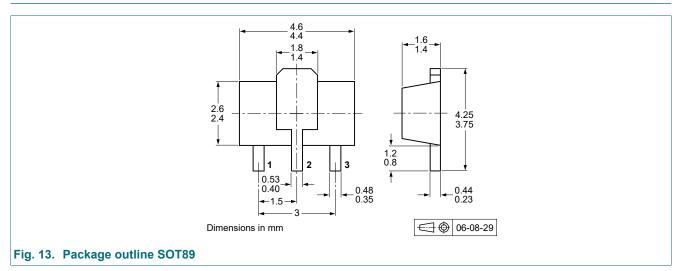
### 11. Test information

#### **Quality information**

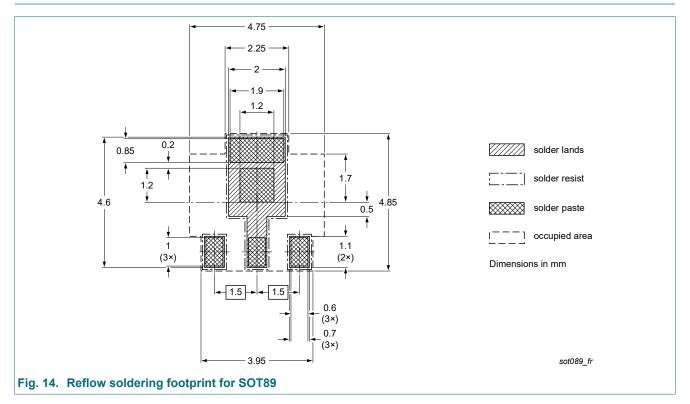
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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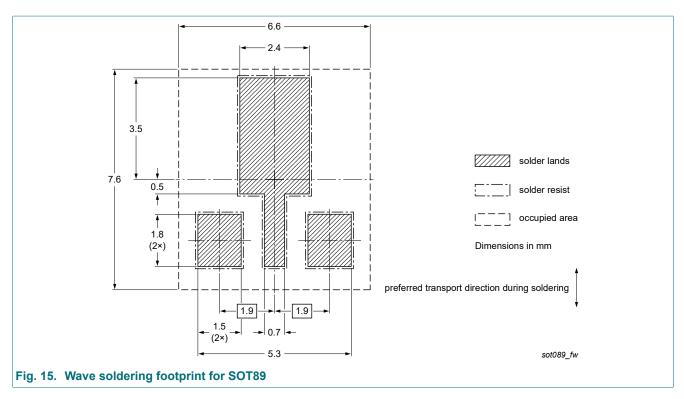
# 12. Package outline



### 13. Soldering



#### 12 V, 5.3 A NPN low VCEsat transistor



# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS301NX-Q v.1	20240206	Product data sheet	-	-		

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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# Contents

1.	General description	.1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	.1
5.	Pinning information	.2
6.	Ordering information	.2
7.	Marking	2
8.	Limiting values	2
9.	Thermal characteristics	3
10.	Characteristics	5
11.	Test information	.7
12.	Package outline	8
13.	Soldering	8
14.	Revision history1	0
	Legal information1	

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